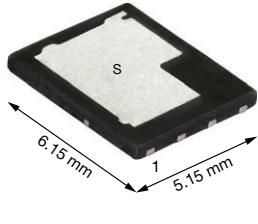
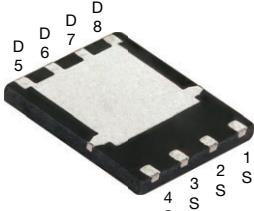


N-Channel 25 V (D-S) 175 °C MOSFET

PowerPAK® SO-8DC


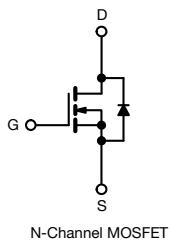
Top View



Bottom View

FEATURES

- TrenchFET® Gen IV power MOSFET
- Optimized Q_g , Q_{gd} , and Q_{gd}/Q_{gs} ratio reduces switching related power loss
- Top side cooling feature provides additional venue for thermal transfer
- 100 % R_g and UIS tested
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912


RoHS
COMPLIANT
HALOGEN
FREE

PRODUCT SUMMARY

V_{DS} (V)	25
$R_{DS(on)}$ max. (Ω) at $V_{GS} = 10$ V	0.00058
$R_{DS(on)}$ max. (Ω) at $V_{GS} = 4.5$ V	0.00082
Q_g typ. (nC)	61
I_D (A)	415
Configuration	Single

APPLICATIONS

- Synchronous rectification
- High power density DC/DC
- Synchronous buck converter
- OR-ing
- Load switching
- Battery management

ORDERING INFORMATION

Package	PowerPAK SO-8DC
Lead (Pb)-free and halogen-free	SiDR220EP-T1-RE3

ABSOLUTE MAXIMUM RATINGS ($T_A = 25$ °C, unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNIT
Drain-source voltage	V_{GS}	V_{DS}	25	V
Gate-source voltage		V_{GS}	+16 / -12	
Continuous drain current ($T_J = 150$ °C)	$T_C = 25$ °C	I_D	415	A
	$T_C = 70$ °C		347	
	$T_A = 25$ °C		92.8 b, c	
	$T_A = 70$ °C		77.6 b, c	
Pulsed drain current ($t = 100$ µs)		I_{DM}	500	A
Continuous source-drain diode current	$T_C = 25$ °C	I_S	136	
	$T_A = 25$ °C		6.8 b, c	
Single pulse avalanche current	$L = 0.1$ mH	I_{AS}	60	mJ
Single pulse avalanche energy		E_{AS}	180	
Maximum power dissipation	$T_C = 25$ °C	P_D	150	W
	$T_C = 70$ °C		105	
	$T_A = 25$ °C		6.25 b, c	
	$T_A = 70$ °C		4 b, c	
Operating junction and storage temperature range		T_J, T_{stg}	-55 to +175	°C
Soldering recommendations (peak temperature) ^c			260	

THERMAL RESISTANCE RATINGS

PARAMETER		SYMBOL	TYPICAL	MAXIMUM	UNIT
Maximum junction-to-ambient ^b	$t \leq 10$ s	R_{thJA}	15	20	°C/W
Maximum junction-to-case (drain)	Steady state	R_{thJC}	0.8	1	
Maximum junction-to-case (source)	Steady state	R_{thJC}	1.1	1.4	

Notes

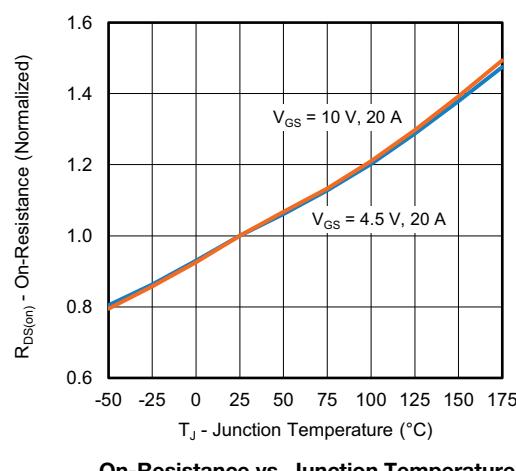
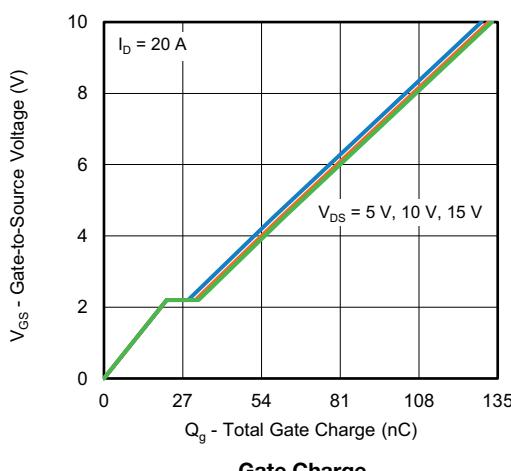
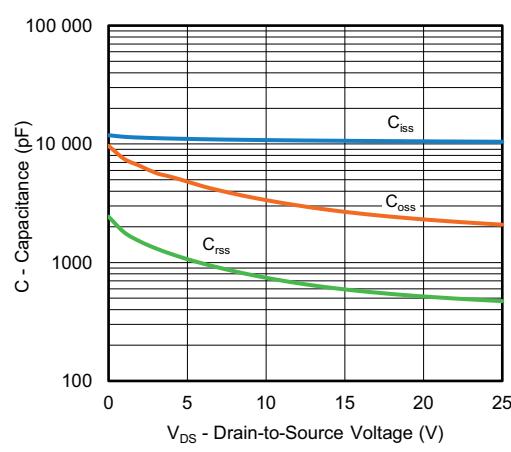
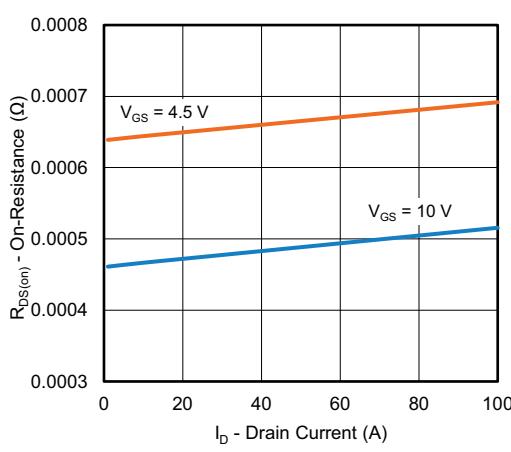
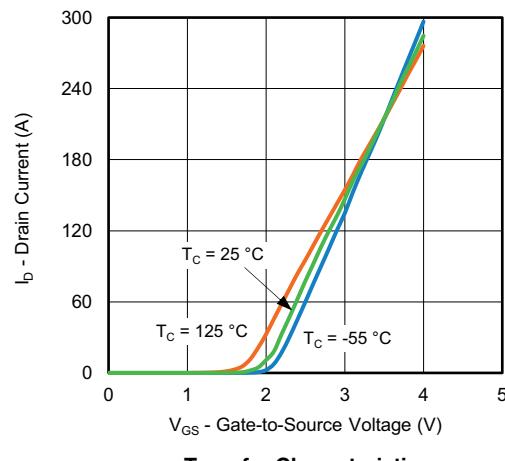
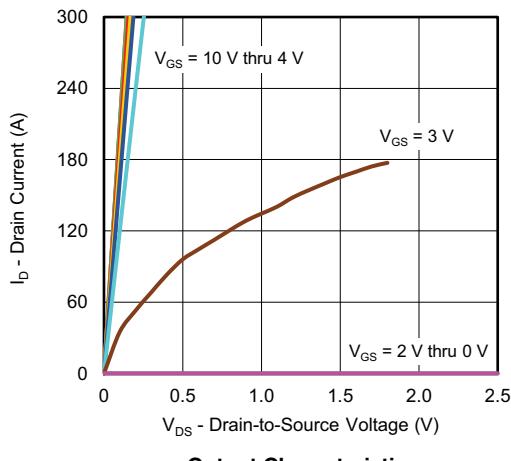
- Package limited
- Surface mounted on 1" x 1" FR4 board
- $t = 10$ s
- See solder profile (www.vishay.com/doc?73257). The PowerPAK SO-8DC is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection
- Rework conditions: manual soldering with a soldering iron is not recommended for leadless components
- Maximum under steady state conditions is 54 °C/W
- $T_C = 25$ °C

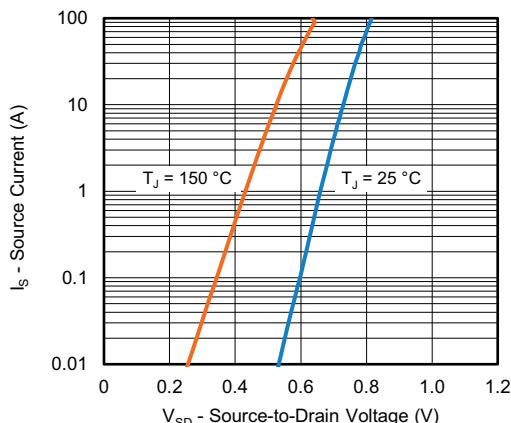
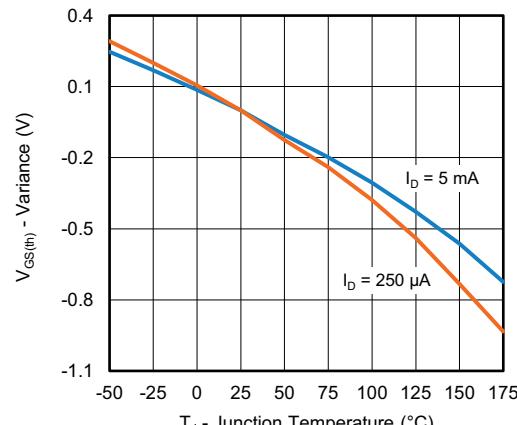
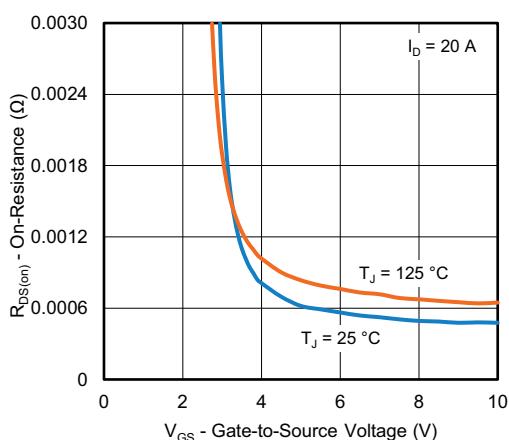
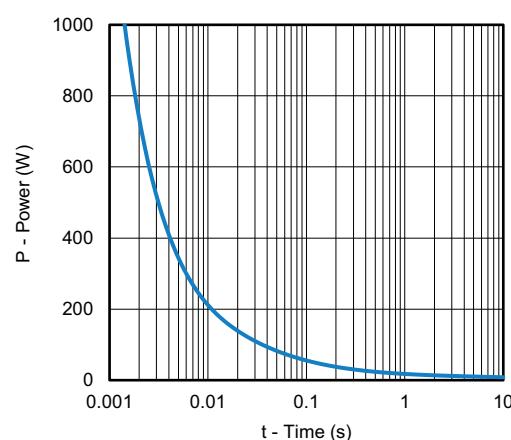
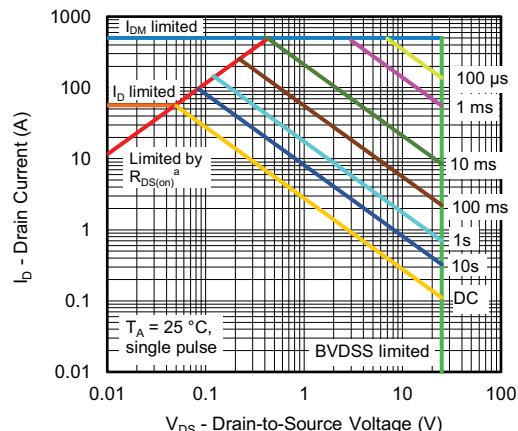
SPECIFICATIONS ($T_J = 25^\circ\text{C}$, unless otherwise noted)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static						
Drain-source breakdown voltage	V_{DS}	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	25	-	-	V
V_{DS} temperature coefficient	$\Delta V_{DS}/T_J$	$I_D = 10 \text{ mA}$	-	21	-	$\text{mV}/^\circ\text{C}$
$V_{GS(\text{th})}$ temperature coefficient	$\Delta V_{GS(\text{th})}/T_J$	$I_D = 250 \mu\text{A}$	-	-4.8	-	
Gate-source threshold voltage	$V_{GS(\text{th})}$	$V_{DS} = V_{GS}, I_D = 250 \mu\text{A}$	1	-	2.1	V
Gate-source leakage	I_{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = +16 / -12 \text{ V}$	-	-	100	nA
Zero gate voltage drain current	I_{DSS}	$V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V}$	-	-	1	μA
		$V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V}, T_J = 70^\circ\text{C}$	-	-	15	
Drain-source on-state resistance ^a	$R_{DS(\text{on})}$	$V_{GS} = 10 \text{ V}, I_D = 20 \text{ A}$	-	0.00048	0.00058	Ω
		$V_{GS} = 4.5 \text{ V}, I_D = 20 \text{ A}$	-	0.00065	0.00082	
Forward transconductance ^a	g_{fs}	$V_{DS} = 15 \text{ V}, I_D = 20 \text{ A}$	-	110	-	S
Dynamic b						
Input capacitance	C_{iss}	$V_{DS} = 10 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$	-	10 850	-	pF
Output capacitance	C_{oss}		-	3360	-	
Reverse transfer capacitance	C_{rss}		-	720	-	
Total gate charge	Q_g	$V_{DS} = 10 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 20 \text{ A}$	-	134	200	nC
Gate-source charge	Q_{gs}	$V_{DS} = 10 \text{ V}, V_{GS} = 4.5 \text{ V}, I_D = 20 \text{ A}$	-	61	92	
Gate-drain charge	Q_{gd}		-	24	-	
Gate resistance	R_g		-	9.2	-	
Turn-on delay time	$t_{d(on)}$	$V_{DD} = 10 \text{ V}, R_L = 0.5 \Omega, I_D \approx 20 \text{ A}, V_{GEN} = 10 \text{ V}, R_g = 1 \Omega$	0.1	0.38	0.75	Ω
Rise time	t_r		-	19	38	ns
Turn-off delay time	$t_{d(off)}$		-	24	48	
Fall time	t_f		-	53	105	
Turn-on delay time	$t_{d(on)}$		-	9	18	
Rise time	t_r		-	51	100	
Turn-off delay time	$t_{d(off)}$		-	95	190	
Fall time	t_f		-	47	94	
-	-	-	-	16	32	
Drain-Source Body Diode Characteristics						
Continuous source-drain diode current	I_S	$T_C = 25^\circ\text{C}$	-	-	136	A
Pulse diode forward current	I_{SM}		-	-	500	
Body diode voltage	V_{SD}	$I_S = 5 \text{ A}, V_{GS} = 0 \text{ V}$	-	0.71	1.1	V
Body diode reverse recovery time	t_{rr}	$I_F = 20 \text{ A}, dI/dt = 100 \text{ A}/\mu\text{s}, T_J = 25^\circ\text{C}$	-	63	126	ns
Body diode reverse recovery charge	Q_{rr}		-	87	174	nC
Reverse recovery fall time	t_a		-	27	-	
Reverse recovery rise time	t_b		-	36	-	ns

Notes

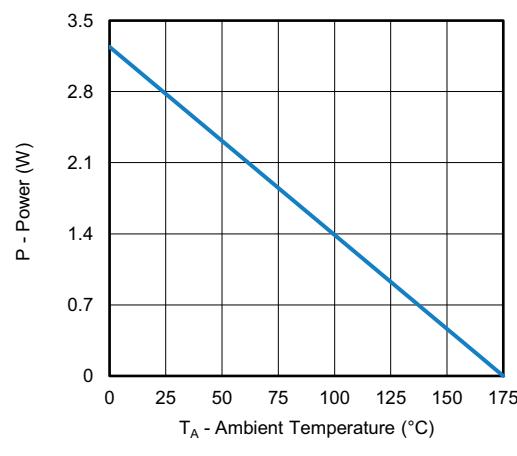
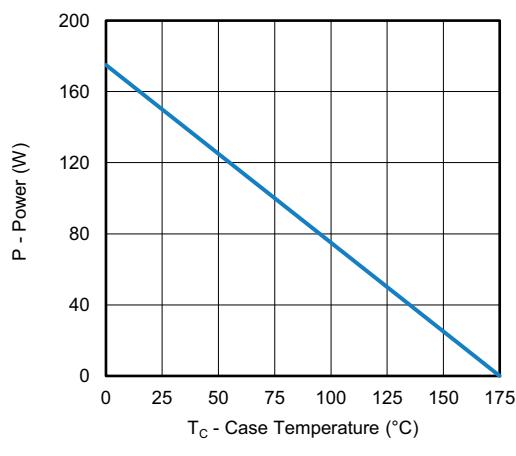
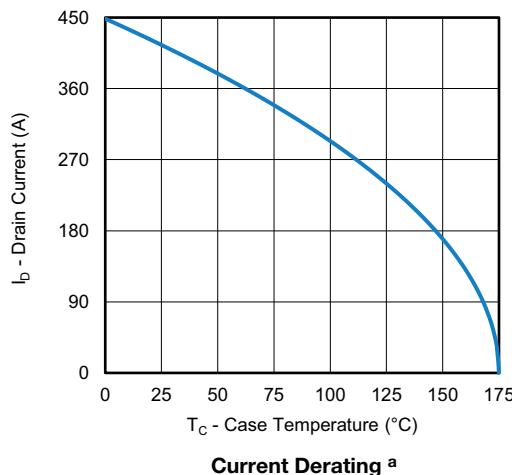
- a. Pulse test; pulse width $\leq 300 \mu\text{s}$, duty cycle $\leq 2\%$
- b. Guaranteed by design, not subject to production testing

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

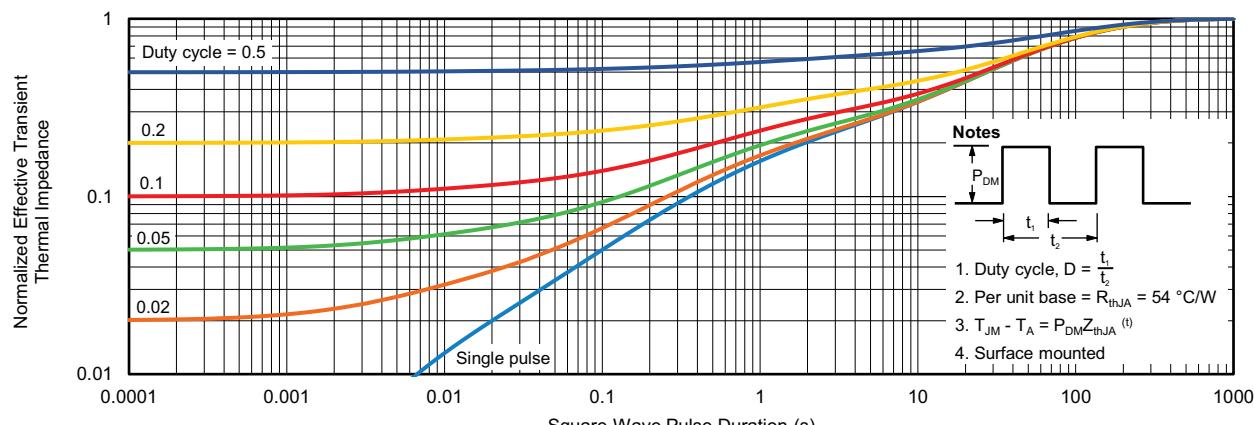
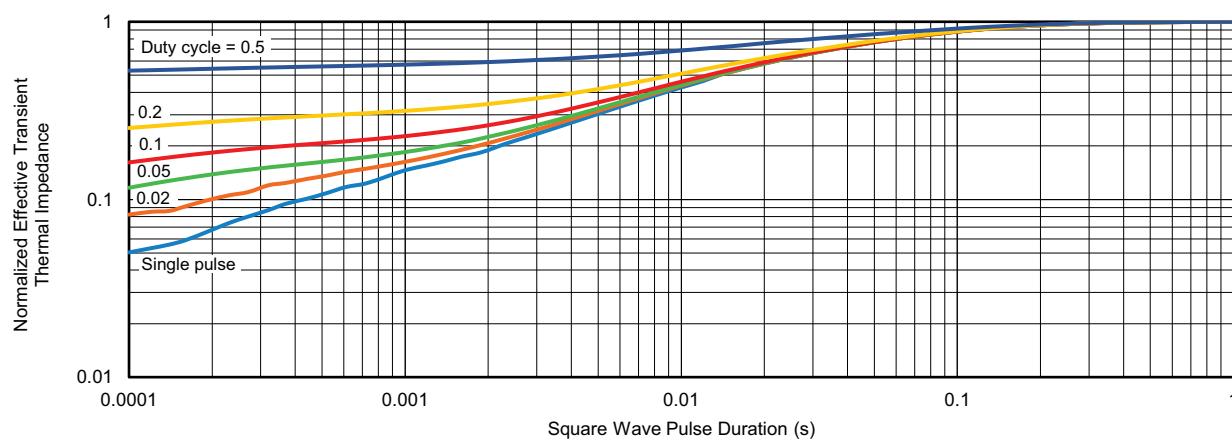
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)


TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

Source-Drain Diode Forward Voltage

Threshold Voltage

On-Resistance vs. Gate-to-Source Voltage

Single Pulse Power, Junction-to-Ambient

Safe Operating Area, Junction-to-Ambient
Note

- a. $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified

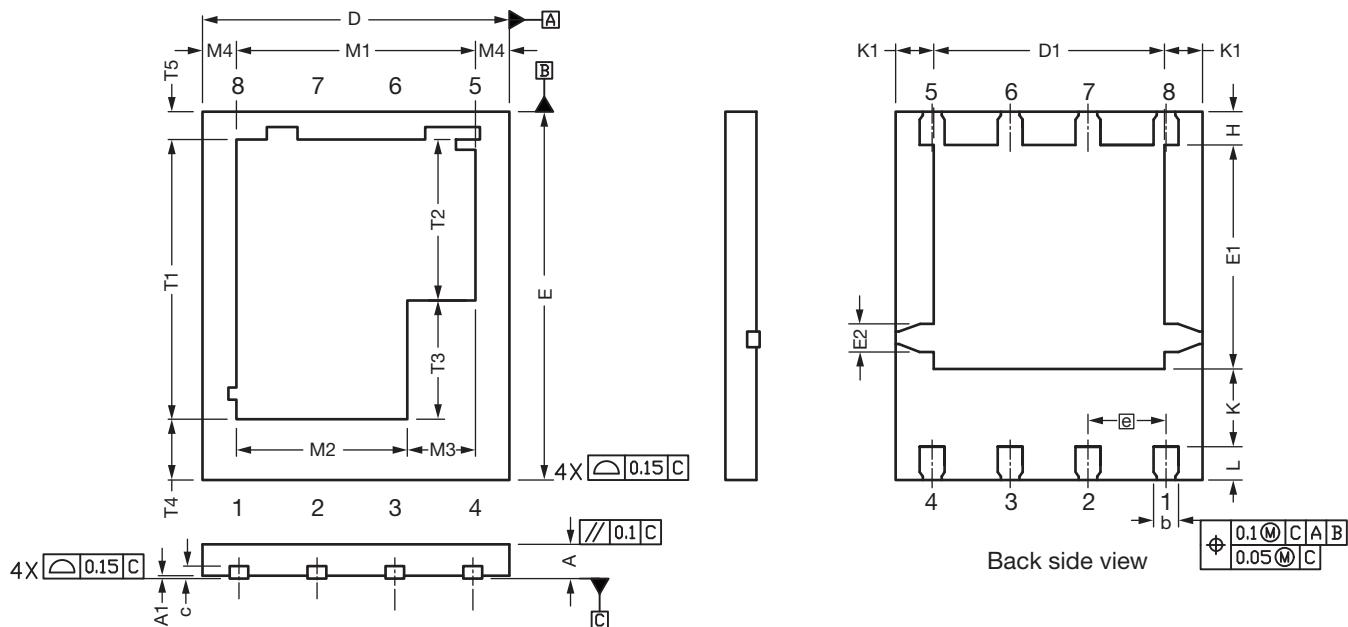
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

Note

- a. The power dissipation P_D is based on T_J max. = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

Normalized Thermal Transient Impedance, Junction-to-Case (Drain)

Normalized Thermal Transient Impedance, Junction-to-Case (Source)

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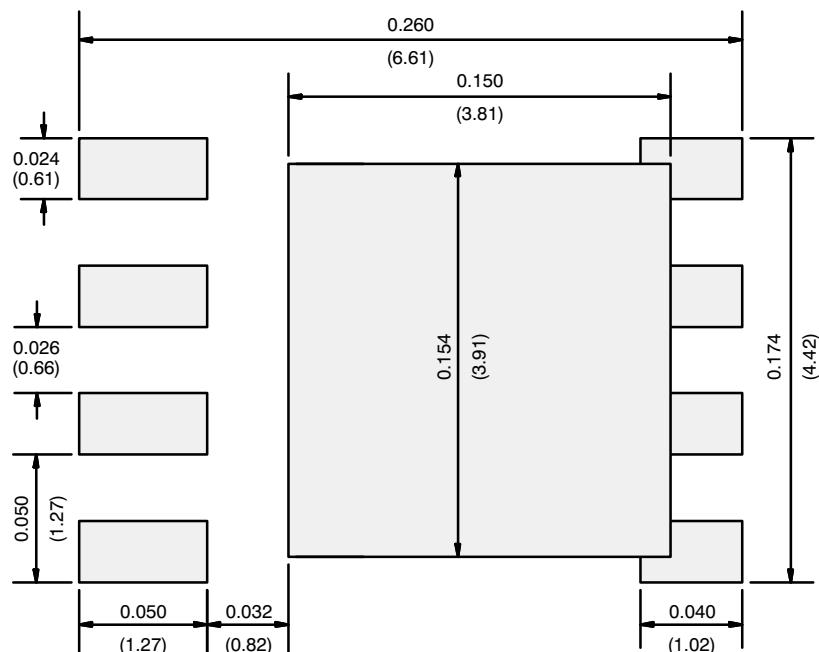
PowerPAK® SO-8 Double Cooling Case Outline



DIM.	MILLIMETERS			INCHES		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A	0.51	0.56	0.61	0.020	0.022	0.024
A1	0.00	0.02	0.05	0.000	0.001	0.002
b	0.36	0.41	0.46	0.014	0.016	0.018
c	0.15	0.20	0.25	0.006	0.008	0.010
D	4.90	5.00	5.10	0.193	0.197	0.201
D1	3.71	3.76	3.81	0.146	0.148	0.150
e	1.27 BSC			0.050 BSC		
E	5.90	6.00	6.10	0.232	0.236	0.240
E1	3.60	3.65	3.70	0.142	0.144	0.146
E2	0.46 typ.			0.018 typ.		
H	0.49	0.54	0.59	0.019	0.021	0.023
K	1.22	1.27	1.32	0.048	0.050	0.052
K1	0.64 typ.			0.025 typ.		
L	0.49	0.54	0.59	0.019	0.021	0.023
M1	3.8	3.90	4.00	0.150	0.154	0.158
M2	2.69	2.79	2.89	0.106	0.110	0.114
M3	1.01	1.11	1.21	0.040	0.044	0.048
M4	0.56 typ.			0.022 typ.		
N	8			8		
T1	4.46	4.56	4.66	0.176	0.180	0.184
T2	2.53	2.63	2.73	0.100	0.104	0.108
T3	1.83	1.93	2.03	0.072	0.076	0.080
T4	0.97 typ.			0.038 typ.		
T5	0.48 typ.			0.019 typ.		

ECN: T24-0304-Rev. C, 29-Jul-2024

DWG: 6048

RECOMMENDED MINIMUM PADS FOR PowerPAK® SO-8 Single

Recommended Minimum Pads
Dimensions in Inches/(mm)

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